

Technical Data Data Sheet N1027, Rev. -

Green Products

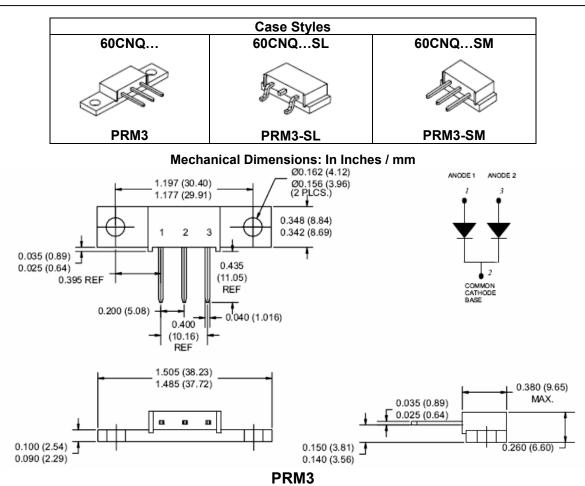
60CNQ035/60CNQ040/60CNQ045 SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

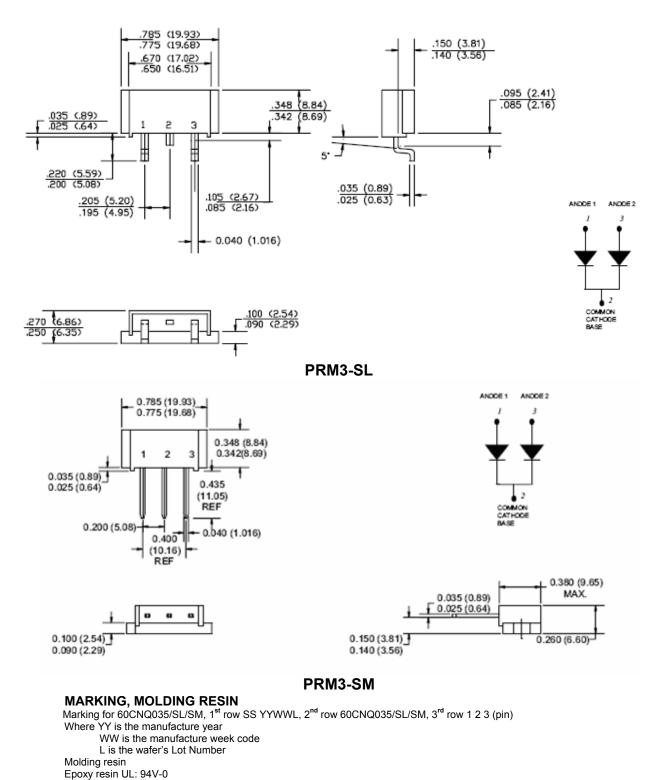
- 150 °C T_J operation
- Center tap module
- Very Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Low profile, high current package
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



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SANGDEST **MICROELECTRONICS**

60CNQ SERIES

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Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	35(60CNQ035) 40(60CNQ040) 45(60CNQ045)	V
Max. Average Forward	I _{F(AV)}	50% duty cycle $@T_c = 116^{\circ}C$, rectangular wave form	60	А
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	1020	А
Non-Repetitive Avalanche Energy(peg leg)	E _{AS}	T _J =25℃,I _{AS} =6A,L=2.2mH	40	mJ
Repetitive Avalanche Current(peg leg)	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T_J max. V_A =1.5× V_R typical	6	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 30A, Pulse, T _J = 25 °C @ 60A, Pulse, T _J = 25 °C	0.55 0.64	V
	V_{F2}	@ 30A, Pulse, T _J = 125 °C @ 60A, Pulse, T _J = 125 °C	0.44 0.59	V
Max. Reverse Current (per leg) *	I _{R1}	$@V_R = rated V_R T_J = 25 \circ C$	5	mA
	I _{R2}	$@V_R = rated V_R T_J = 125 \circ C$	200	mA
Max. Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	2600	pF
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	6.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

* Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

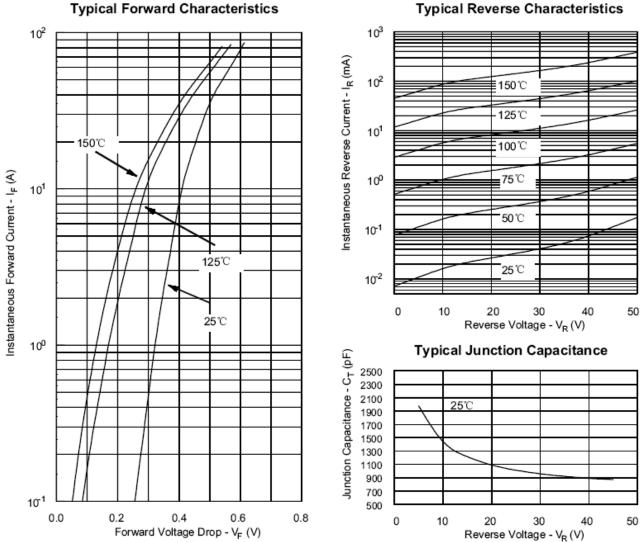
Characteristics	Symbol	Condition	Specification	Units	
Max. Junction Temperature	TJ	-	-55 to +150	°C	
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C	
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ ext{ heta}JC}$	DC operation	0.85	°C/W	
Maximum Thermal Resistance Junction to Case (per package)	$R_{ ext{ heta}JC}$	DC operation	0.42	°C/W	
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.30	°C/W	
Mounting Torque	Тм	-	40(min)	Kg-cm	
			58(max)		
Approximate Weight	wt	-	7.8	g	
Case Style	PRM3 PRM3-SL PRM3-SM				

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